

**MOSFET Example.** Given a MOSFET capacitor with  $\epsilon_r = 25$  on a Si substrate doped  $N_a = 4 \times 10^{17} \text{ cm}^{-3}$  and an insulator dielectric thickness  $d = 110 \text{ \AA}$ , calculate the high frequency  $C_{\text{accumulation}}$ , maximum depletion width  $W_m$ , semiconductor depletion capacitance  $C_d$ , and minimum high frequency capacitance  $C_{\text{min}}$ . Sketch and label the low and high frequency CV behavior.  $\epsilon(\text{Si})=11.8$ ,  $\epsilon_0 = 8.85 \times 10^{-14} \text{ F/cm}$ .  $n_i = 1.5 \times 10^{10}$ .